



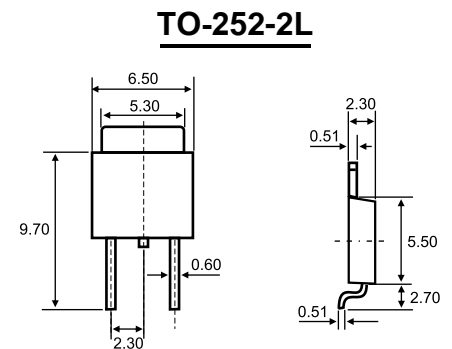
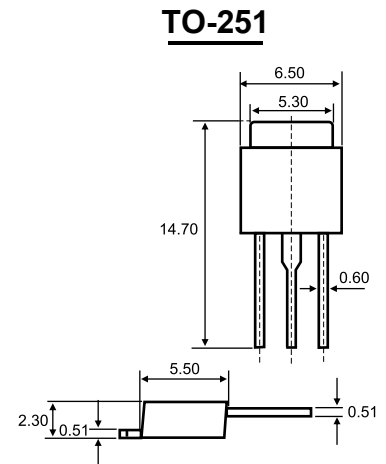
1. BASE
2. COLLECTOR
3. EMITTER

Features

- ◇ Complementary darlington power transistors dpak for surface mount applications

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JC}$	Thermal resistance, junction to case	6.25	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal resistance, junction to Ambient	71.4	$^\circ\text{C/W}$
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



Dimensions in inches and (millimeters)

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30\text{mA}, I_B=0$	100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=5\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=100\text{V}, I_E=0$			20	μA
Collector-emitter cut-off current	I_{CEO}	$V_{CE}=50\text{V}, I_E=0$			20	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			2	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=3\text{V}, I_C=500\text{mA}$	500			
	$h_{FE(2)}$	$V_{CE}=3\text{V}, I_C=2\text{A}$	1000		12000	
	$h_{FE(3)}$	$V_{CE}=3\text{V}, I_C=4\text{A}$	200			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=2\text{A}, I_B=8\text{mA}$			2	V
	$V_{CE(sat)2}$	$I_C=4\text{A}, I_B=40\text{mA}$			3	V
Base-emitter voltage	V_{BE}	$V_{CE}=3\text{V}, I_C=2\text{A}$			2.8	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=0.75\text{A}, f=1\text{MHz}$	25			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$			100	pF

Typical Characteristics

